

O I P E  
JAN 28 2004 Docket No.: 57810-077

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of : Customer Number: 20277  
Yasuhiko NOMURA, et al. : Confirmation Number: 3966  
Serial No.: 10/663,707 : Group Art Unit: 2828  
Filed: September 17, 2003 : Examiner:  
For: NITRIDE-BASED SEMICONDUCTOR LASER DEVICE

INFORMATION DISCLOSURE STATEMENT

Mail Stop IDS  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

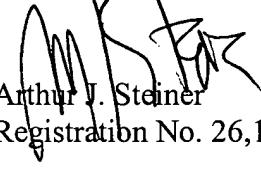
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**10/663,707**

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Respectfully submitted,

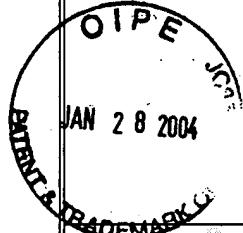
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**INFORMATION DISCLOSURE  
CITATION IN AN  
APPLICATION**



(PTO-1449)

ATTY. DOCKET NO.  
**57810-077**SERIAL NO.  
**10/663,707**APPLICANT  
Yasuhiko NOMURA, et al.FILING DATE  
**September 17, 2003**GROUP  
**2828****U.S. PATENT DOCUMENTS**

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code <sup>2</sup> ( <i>if known</i> )	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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**FOREIGN PATENT DOCUMENTS**

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Code <sup>3</sup> -Number & Kind Codes ( <i>if known</i> )	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
		JP 2002-124737	04/26/2002	SANYO ELECTRIC CO LTD		JAPAN (w/English Abstract)	
		JP 2002-299768	10/11/2002	MATSUSHITA ELECTRIC IND CO LTD		JAPAN (w/English Abstract)	
		JP 2001-57461	02/27/2001	NICHIA CHEM IND LTD		JAPAN (w/English Abstract)	
		JP 11-340580	12/10/1999	FUJITSU LTD		JAPAN (w/English Abstract)	
		JP 10-294529	11/4/1998	TOSHIBA CORP.		JAPAN (w/English Abstract)	

**OTHER ART** (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
		Nishinaga Tatau, "Hetero-epitaxy with Large Lattice Mismatch and Microchannel Epitaxy of Compound Semiconductor." Department of Electronic Engineering, Graduate School of Engineering, Volume 21, No. 6, pp. 320-325, 2000	
		H. Amano, et al. "Metalorganic vapor phase epitaxial growth of a high quality GaN film using an AlN buffer layer." Appl. Phys. Lett., Vol. 48, No. 5, 3 February 1986, pp. 353-355	

EXAMINER

DATE CONSIDERED

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.